



INFORMATION DISCLOSURE STATEMENT BY APPLICANT PTO-1449	DOCKET NO. 01381/8	SERIAL NO. 10/509,923
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	FILING DATE October 1, 2004	GROUP Not Yet Assigned

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT/PUBLICATION NUMBER	PATENT/PUBLICATION DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>AM</i>	5,958,132	September 28, 1999	Takahashi et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						Yes	No
<i>AM</i>	JP 10-17399	January 20, 1998	Japan			Abstract	
<i>AM</i>	JP 11-106297	April 20, 1999	Japan			Abstract	

OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<i>AM</i>	Yu. M. Tairov and V. F. Tsvetkov, General Principles of Growing Large-Size Single Crystals of Various Silicon Carbide Polytypes, Journal Of Crystal Growth, Vol. 52 (1981) pp. 146-150.
<i>AM</i>	P. G. Neudeck et al., Performance Limiting Micropipe Defects in Silicon Carbide Wafers, IEEE Electron Device Letters, Vol. 15 (1994) pp. 63-65.
<i>AM</i>	T. Kimoto et al., Performance Limiting Surface Defects in SiC Epitaxial p-n Junction Diodes, IEEE Tran. Electron. Devices, Vol. 46 (1999) pp. 471-477.
<i>AM</i>	J. Takahashi et al., Sublimation Growth of SiC Single Crystalline Ingots on faces Perpendicular to the (0001) Basal Plane, J. Cryst. Growth, Vol. 135 (1994) pp. 61-70.
<i>AM</i>	H. Yano et al., Anisotropy of Inversion Channel Mobility in 4H- and 6H-SiC MOSFETs on (1120) Face, Materials Science Forum, Vol. 338-342 (2000) pp. 1105-1108.
<i>AM</i>	J. Takahashi et al., Sublimation Growth of 6H- and 4H-SiC Single Crystals in the [1100] and [1120] Directions, Journal of Crystal Growth, Vol. 181 (1997) pp. 229-240.
<i>AM</i>	J. Takahashi and N. Ohtani, Modified-Lely SiC Crystals Grown in [1100] and [1120] Directions, Phys. Stat. Sol. (b), Vol. 202 (1997) pp. 163-175.
<i>AM</i>	Japanese Patent Application Laid-open No. 5-262599, SiC Single Crystal and Method for Growing the Same, October 12, 1993.

EXAMINER	<i>AM</i>	DATE CONSIDERED <i>9-12-06</i>
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		